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Kind regards,

Team Nexperia

PEMH10; PUMH10

NPN/NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47k Ω

Rev. 3 — 20 December 2011

Product data sheet

1. Product profile

1.1 General description

NPN/NPN Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package		NPN/PNP	PNP/PNP	Package
	NXP	JEITA	ITA complement comp		configuration
PEMH10	SOT666	-	PEMD10	PEMB10	ultra small and flat lead
PUMH10	SOT363	SC-88	PUMD10	PUMB10	very small

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)		1.54	2.20	2.86	kΩ
R2/R1	bias resistor ratio		17	21	26	



2. Pinning information

Table 3. Pinning

Table 3.	rinning			
Pin	Description	Simplified outline	Graphic symbol	
1	GND (emitter) TR1			
2	input (base) TR1	6 5 4	6 5 4	
3	output (collector) TR2			
4	GND (emitter) TR2		R1 R2	
5	input (base) TR2		1 2 3 TR1	TR1
6	input (base) TR2 output (collector) TR1	001aab555	R2 R1	
			sym063	

3. Ordering information

Table 4. Ordering information

Type number	Package	Package	
	Name	Description	Version
PEMH10	-	plastic surface-mounted package; 6 leads	SOT666
PUMH10	SC-88	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PEMH10	10
PUMH10	H*0

[1] * = placeholder for manufacturing site code.

5. Limiting values

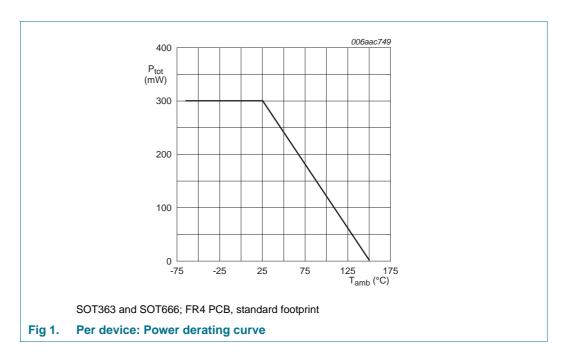
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
V_{I}	input voltage				
	positive		-	+12	V
	negative		-	-5	V
Io	output current		-	100	mA
I _{CM}	peak collector current		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u>		
	PEMH10 (SOT666)		[2] _	200	mW
	PUMH10 (SOT363)		-	200	mW
Per device					
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u>		
	PEMH10 (SOT666)		[2] _	300	mW
	PUMH10 (SOT363)		-	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.



6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transistor						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	PEMH10 (SOT666)		[2] _	-	625	K/W
	PUMH10 (SOT363)		-	-	625	K/W
Per devic	e					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	PEMH10 (SOT666)		[2] _	-	417	K/W
	PUMH10 (SOT363)		-	-	417	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

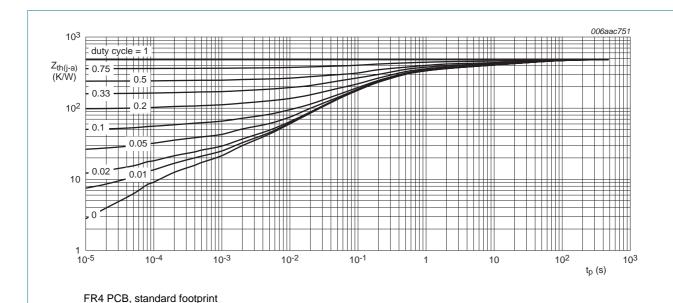


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PEMH10 (SOT666); typical values

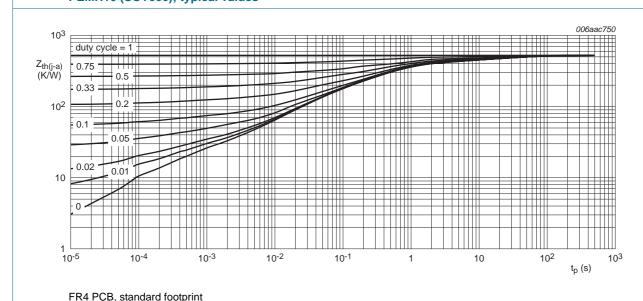


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PUMH10 (SOT363); typical values

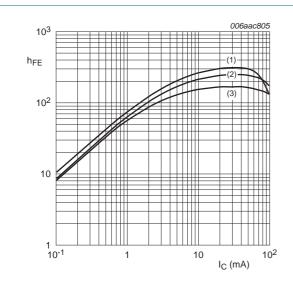
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	100	nA
	cut-off current	$V_{CE} = 30 \text{ V; } I_{B} = 0 \text{ A;}$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	5	μА
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	180	μА
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}$	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}$	-	-	100	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	0.6	0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 5 \text{ mA}$	1.1	0.75	-	V
R1	bias resistor 1 (input)		1.54	2.20	2.86	kΩ
R2/R1	bias resistor ratio		17	21	26	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2.5	pF
f _T	transition frequency	$V_{CB} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	[1] -	230	-	MHz

^[1] Characteristics of built-in transistor.

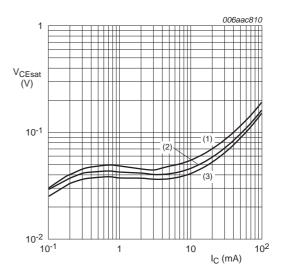


(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 4. DC current gain as a function of collector current; typical values



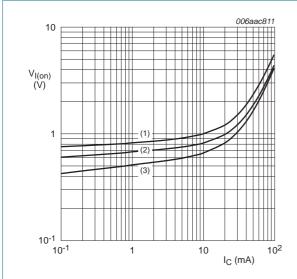
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



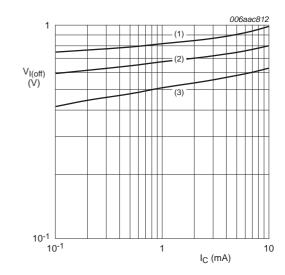
$$V_{CE} = 0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 6. On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. Off-state input voltage as a function of collector current; typical values

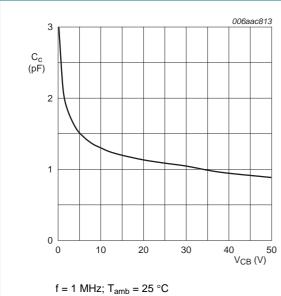


Fig 8. Collector capacitance as a function of collector-base voltage; typical values

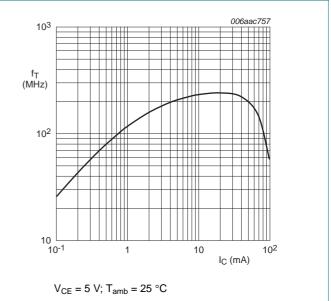


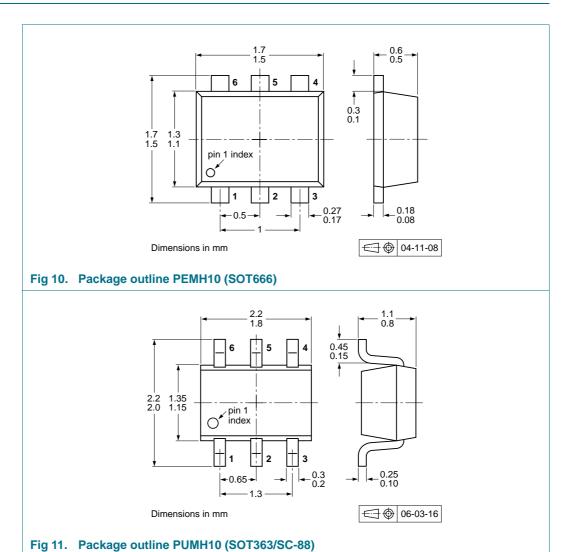
Fig 9. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

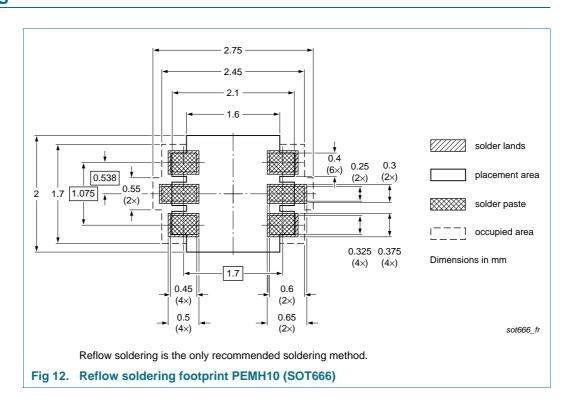
Table 9. Packing methods

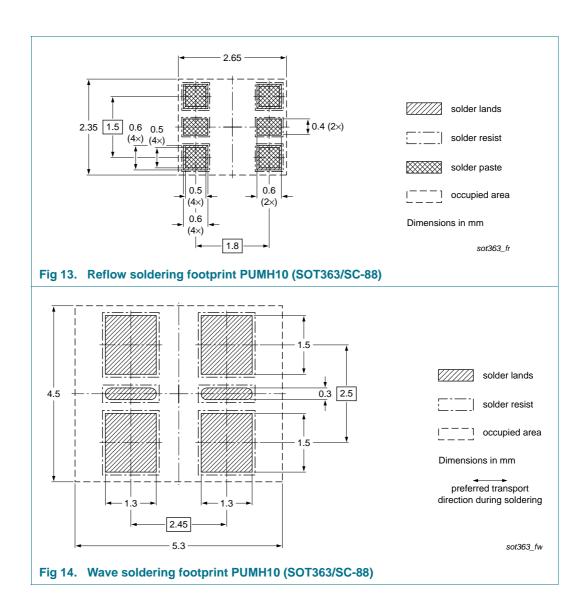
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packi	ng quai	ntity	
				3000	4000	8000	10000
PEMH10	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-
		4 mm pitch, 8 mm tape and reel		-	-115	-	-
PUMH10	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165

- [1] For further information and the availability of packing methods, see Section 14.
- [2] T1: normal taping
- [3] T2: reverse taping

11. Soldering





12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMH10_ PUMH10 v.3	20111220	Product data sheet	-	PEMH10_ PUMH10 v.2
Modifications:	guidelines of Legal texts hat Section 1 "Profession 4" Materials and a section 10" Particular and a section 1	added st information": added at 11: replaced by minimize acking information": added oldering": added egal information": updated	ew company name who red according to the latest according to the latest oltage, V _{i(on)} redefined d package outline draw	est measurements measurements, f _T added, to V _{I(on)} on-state input
PEMH10_ PUMH10 v.2	20031020	Product data sheet	-	PEMH10 v.1 PUMH10 v.1
PEMH10 v.1	20011022	Preliminary specification	on -	<u>-</u>
PUMH10 v.1	20000801	Product specification		-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
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PEMH10_PUMH10

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PEMH10; PUMH10

NPN/NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47k Ω

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